ABSTRACT OF THE DISCLOSURE

A semiconductor device having a semiconductor substrate, at least one of a protruding electrode and wiring formed on one surface of the semiconductor substrate, and a first resin film formed on this surface. The first resin film has elasticity low enough to reduce stress induced by a difference in thermal expansion coefficient between the semiconductor substrate and the first resin film. A second resin film, having higher elasticity or higher strength than the first resin film, may be formed on the other surface of the semiconductor substrate.